

High Speed IGBT

IXSP 20N60B2 IXSP 20N60B2D1

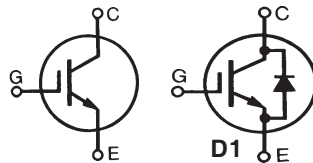
$$V_{CES} = 600 \text{ V}$$

$$I_{C25} = 35 \text{ A}$$

$$V_{CE(sat)} = 2.5 \text{ V}$$

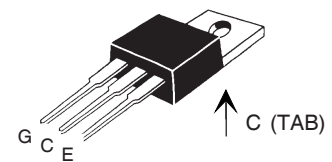
Short Circuit SOA Capability

Preliminary Data Sheet



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	35	A
I_{C110}	$T_C = 110^\circ\text{C}$	20	A
$I_{F(110)}$		11	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	60	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 82 \Omega$ Clamped inductive load	$I_{CM} = 32$ @ $0.8 V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = 15 \text{ V}$, $V_{CE} = 360 \text{ V}$, $T_J = 125^\circ\text{C}$ $R_G = 82 \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	190	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Weight		2	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
Maximum tab temperature for soldering for 10s		260	$^\circ\text{C}$

TO-220AB (IXSP)



G = Gate C = Collector
E = Emitter TAB = Collector

Features

- International standard package
- Guaranteed Short Circuit SOA capability
- Low $V_{CE(sat)}$
 - for low on-state conduction losses
- High current handling capability
- MOS Gate turn-on
 - drive simplicity
- Fast fall time for switching speeds up to 20 kHz

Applications

- AC motor speed control
- Uninterruptible power supplies (UPS)
- Welding

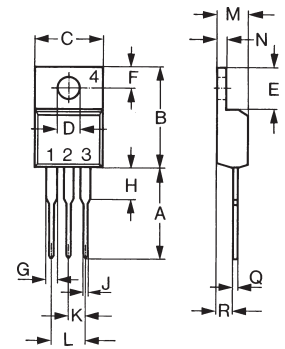
Advantages

- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}$, $V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 750 \mu\text{A}$, $V_{CE} = V_{GE}$	3.5		V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$	SP20N60B2		25 μA
		SP20N60B2D1		85 μA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = 16 \text{ A}$, $V_{GE} = 15 \text{ V}$			2.5 V

DS99181A(07/04)

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = 16\text{A}; V_{CE} = 10\text{V}$, Note 1	3.5	7.0	S
C_{ies}			800	pF
C_{oes}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$ $f = 1\text{MHz}$		76	pF
C_{res}	20N60B2D1		90	pF
			28	pF
Q_g			33	nC
Q_{ge}	$I_C = 16\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 V_{CES}$		12	nC
Q_{gc}			12	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$		30	ns
t_{ri}	$I_C = 16\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.8 V_{CES}, R_G = 10\ \Omega$		30	ns
$t_{d(off)}$	Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G		116	ns
t_{fi}			126	ns
E_{off}			380	600 μJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$		30	ns
t_{ri}			30	ns
E_{on}	$I_C = 16\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.8 V_{CES}, R_G = 10\ \Omega$	20N60B2 20N60B2D1	0.12	mJ
	Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G		0.42	mJ
$t_{d(off)}$			180	ns
t_{fi}			210	ns
E_{off}			970	μJ
R_{thJC}				0.66 K/W
R_{thCS}			0.3	K/W

TO-220 AB (IXSP) Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = 10\text{A}, V_{GE} = 0\text{V}$	$T_J = 150^\circ\text{C}$		1.66 V 2.66 V
I_{RM}	$I_F = 12\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$	$T_J = 100^\circ\text{C}$	1.5	A
t_{rr}	$V_R = 100\text{V}$	$T_J = 100^\circ\text{C}$	90	ns
t_{rr}	$I_F = 1\text{A}; -di/dt = 100\text{A}/\mu\text{s}; V_R = 30\text{V}$		30	ns
R_{thJC}				2.5 K/W

Note 1: Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,381,025 6,162,665 6,306,728 B1 6,534,343 6,683,344 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,486,715 6,259,123 B1 6,404,065 B1 6,583,505 6,710,405 B2

Fig. 1. Output Characteristics @ 25 °C

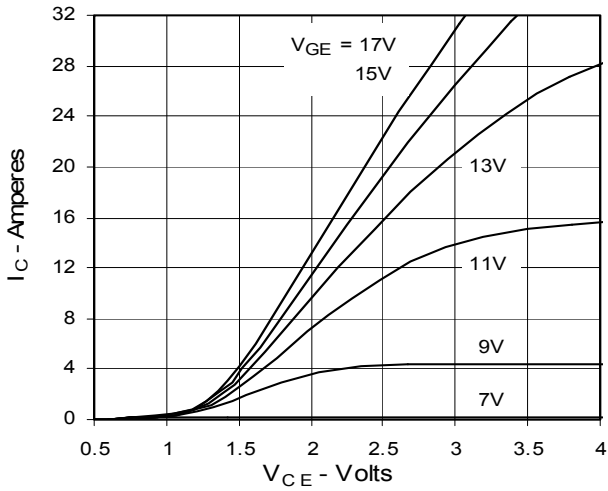


Fig. 2. Extended Output Characteristics @ 25 °C

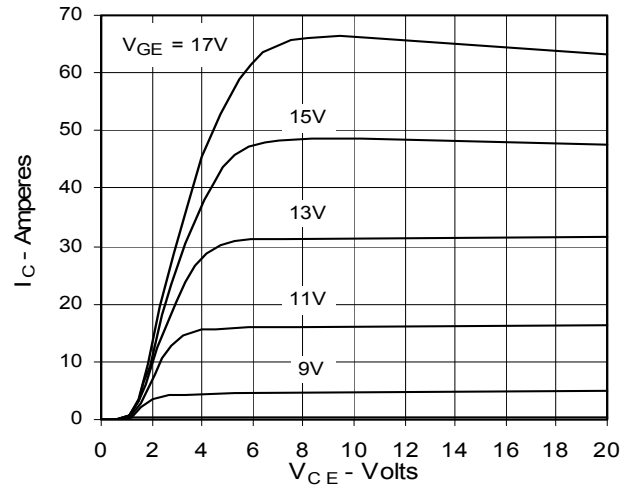


Fig. 3. Output Characteristics @ 125 °C

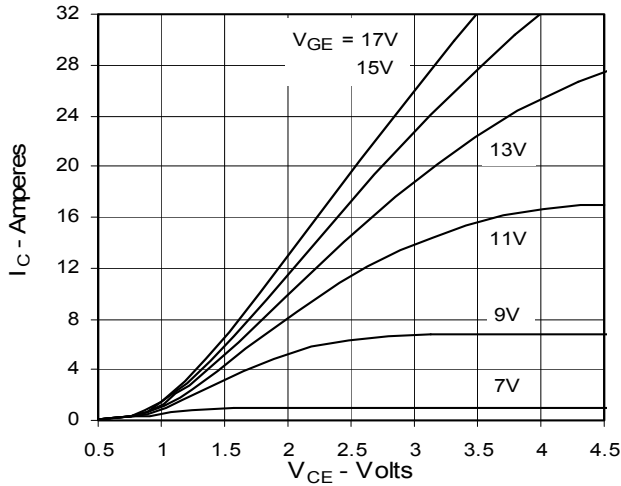


Fig. 4. Dependence of $V_{CE(sat)}$ on Temperature

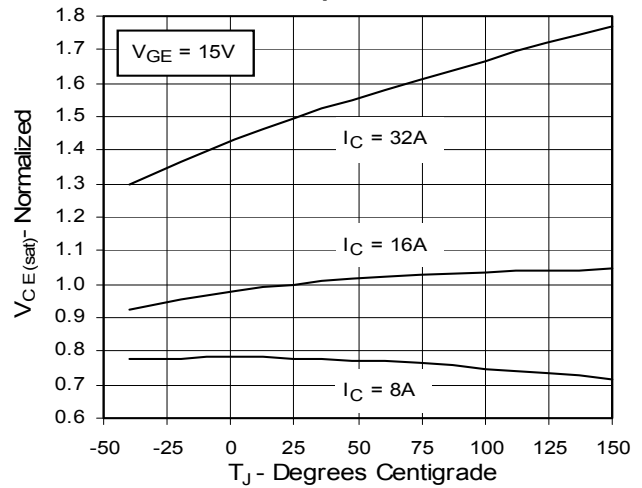


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter voltage

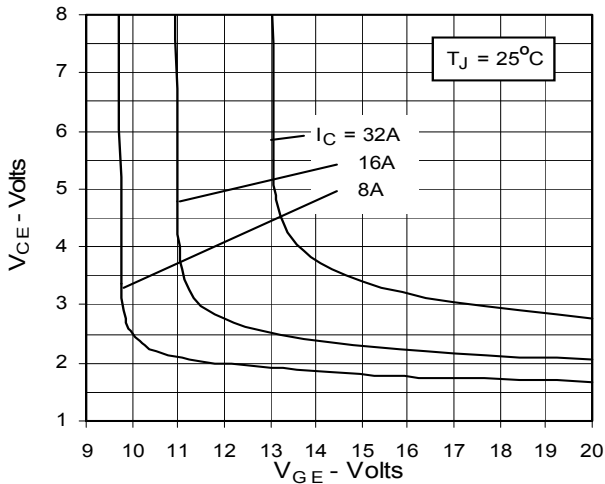


Fig. 6. Input Admittance

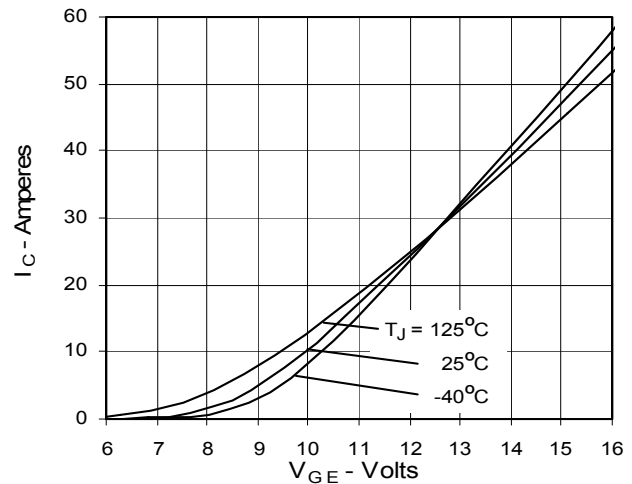


Fig. 7. Transconductance

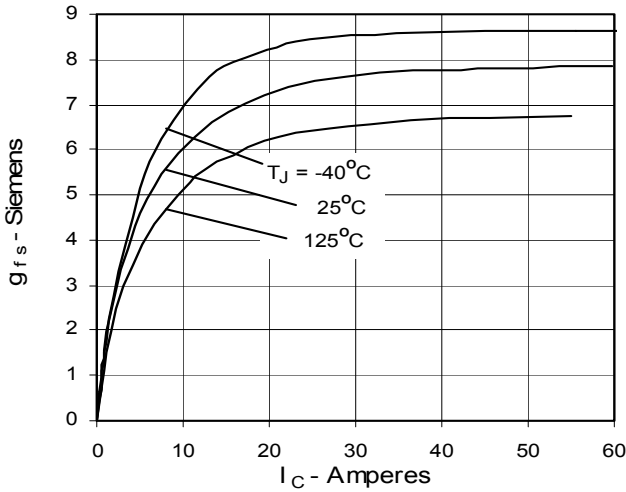


Fig. 8. Dependence of Turn-off Energy Loss on R_G

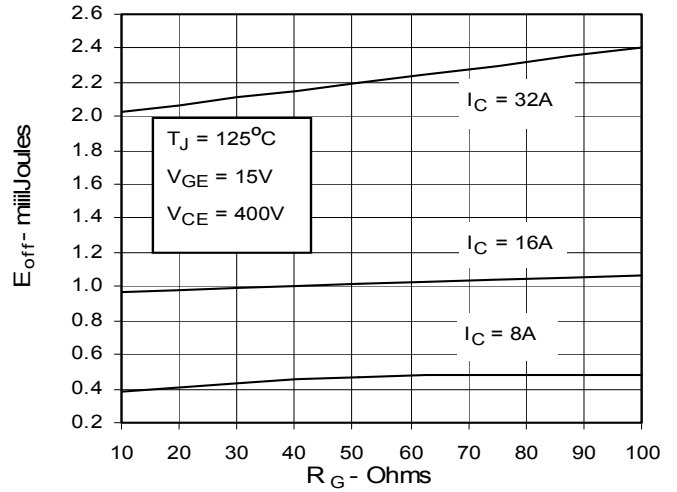


Fig. 9. Dependence of Turn-Off Energy Loss on I_C

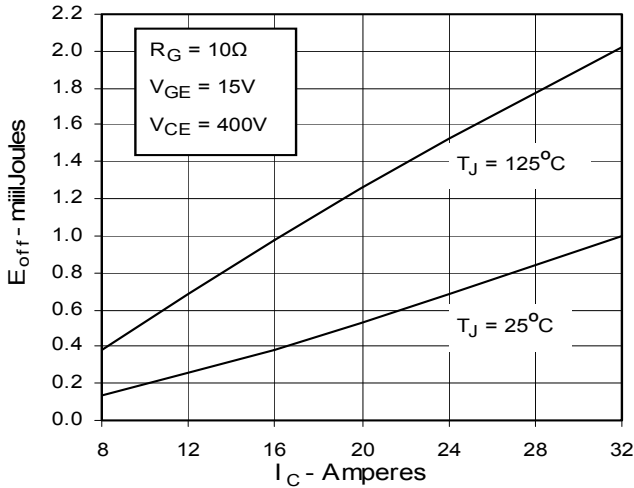


Fig. 10. Dependence of Turn-off Energy Loss on Temperature

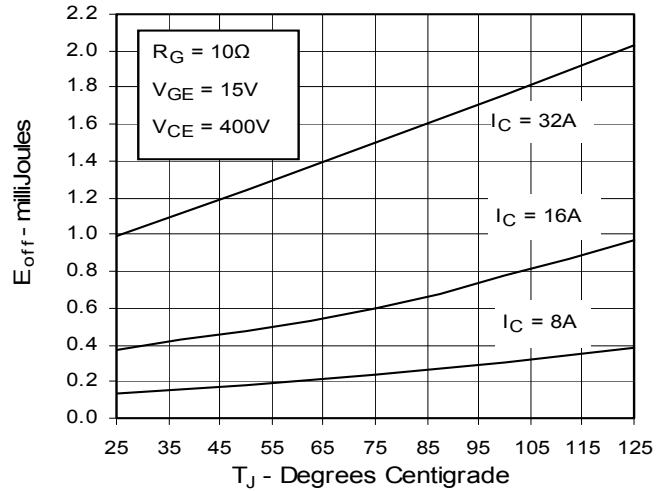


Fig. 11. Dependence of Turn-off Switching Time on R_G

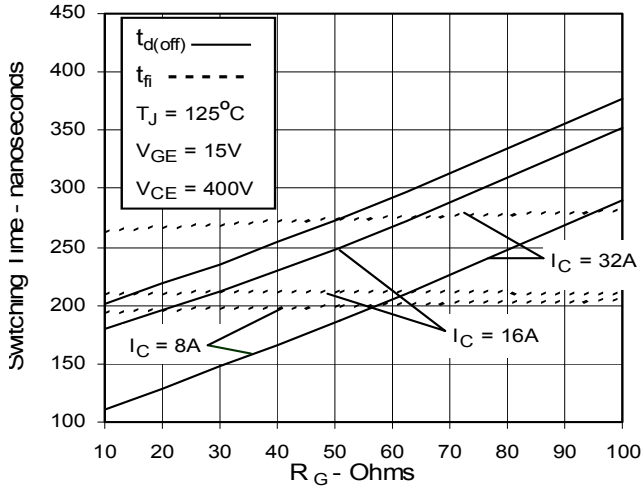


Fig. 12. Dependence of Turn-off Switching Time on I_C

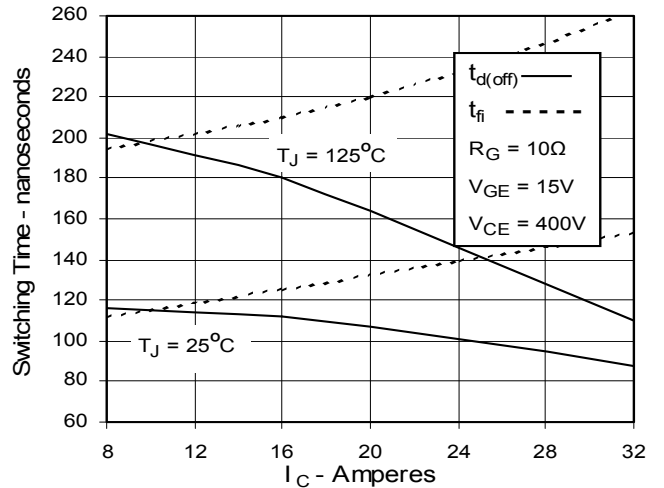


Fig. 13. Dependence of Turn-off Switching Time on Temperature

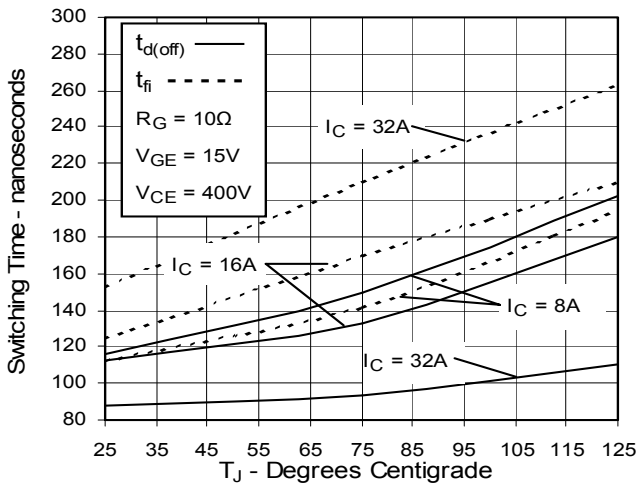


Fig. 14. Gate Charge

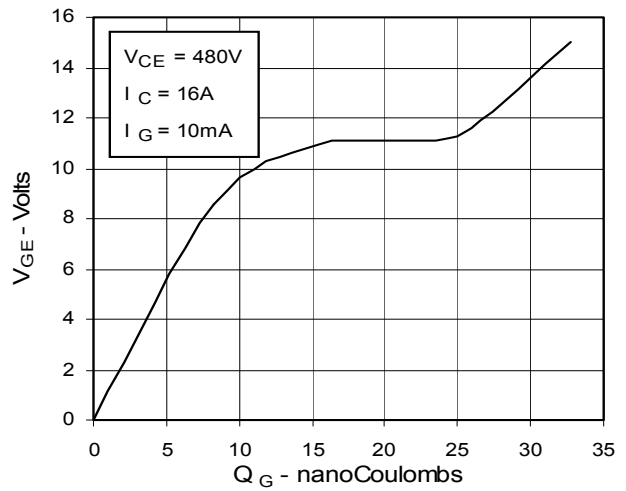


Fig. 15. Capacitance

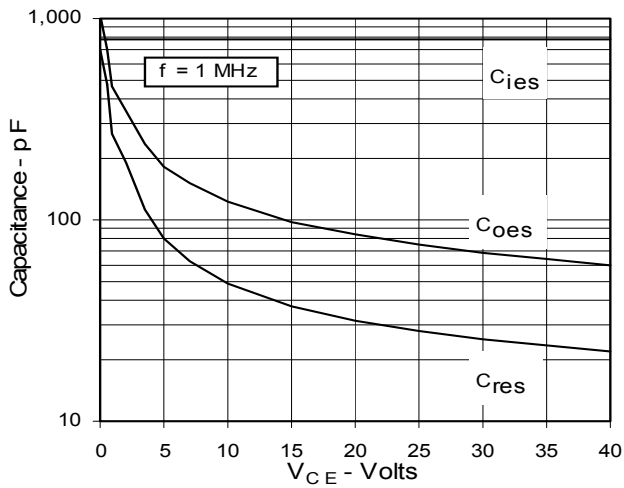


Fig. 16. Reverse-Bias Safe Operating Area

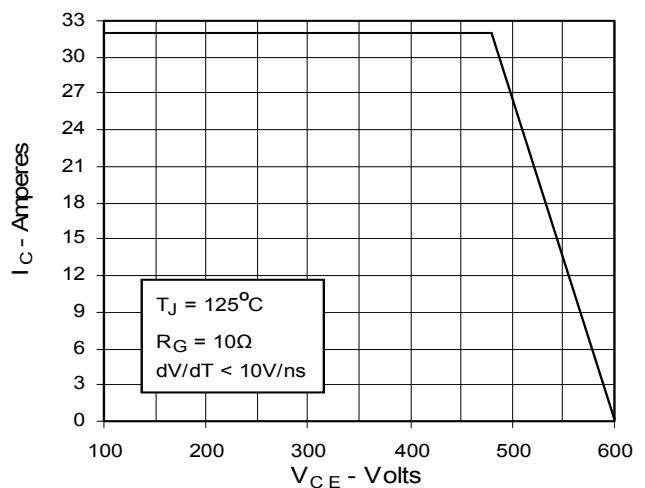
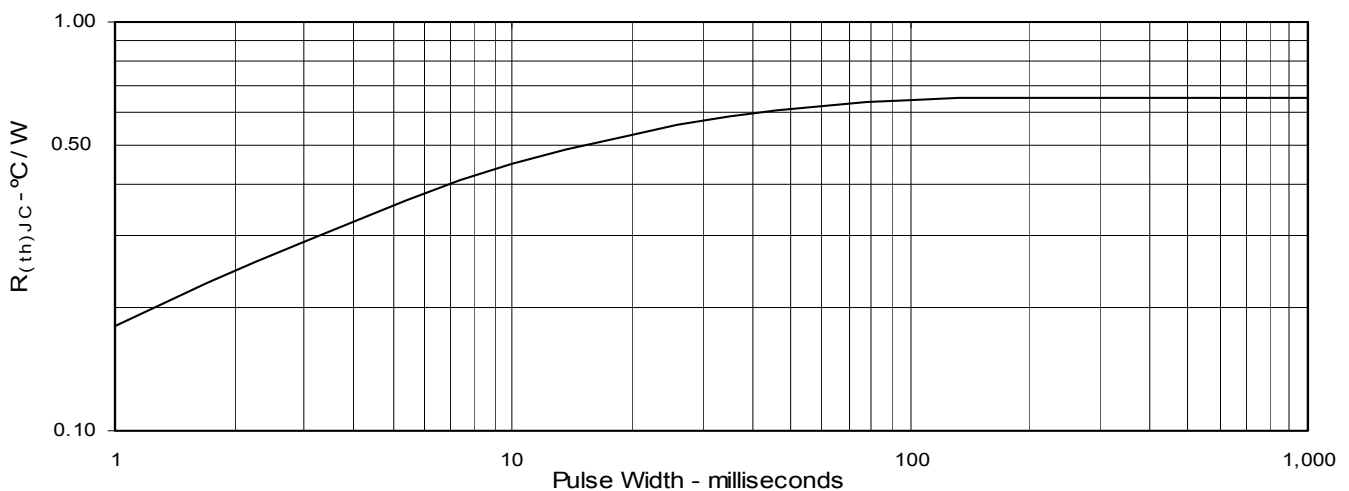


Fig. 17. Maximum Transient Thermal Resistance



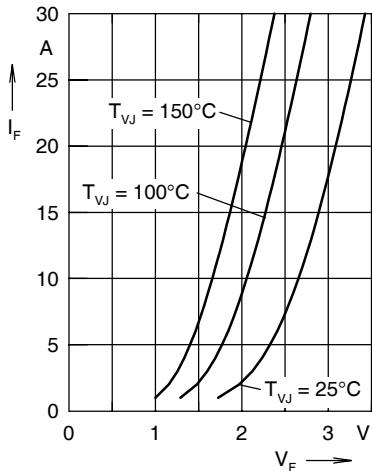


Fig. 18. Forward current I_F versus V_F

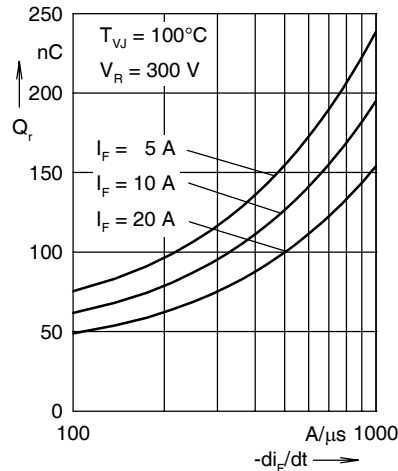


Fig. 19. Reverse recovery charge Q_r

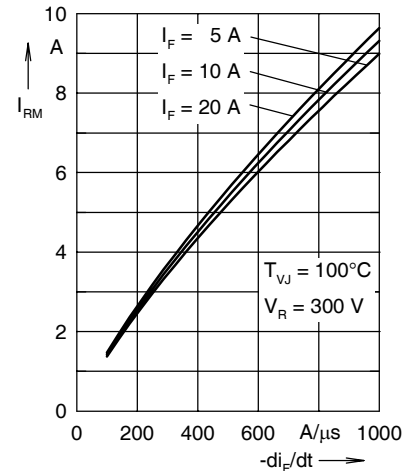


Fig. 20. Peak reverse current I_{RM}

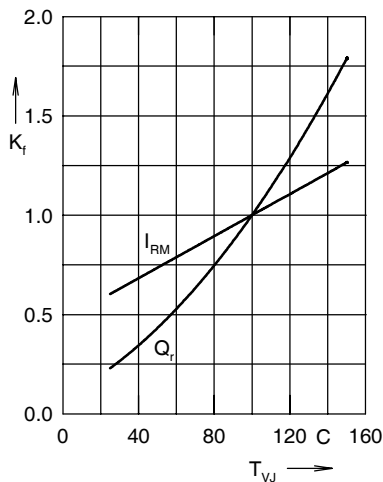


Fig. 21. Dynamic parameters Q_r , I_{RM}

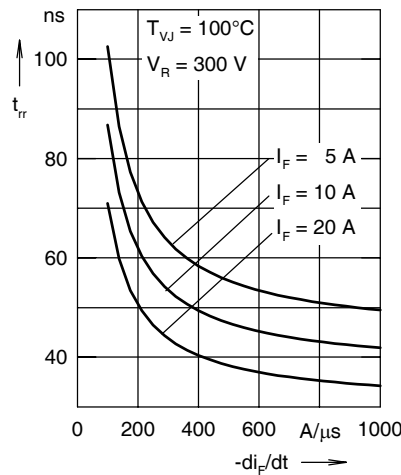


Fig. 22. Recovery time t_{rr} versus $-di_F/dt$

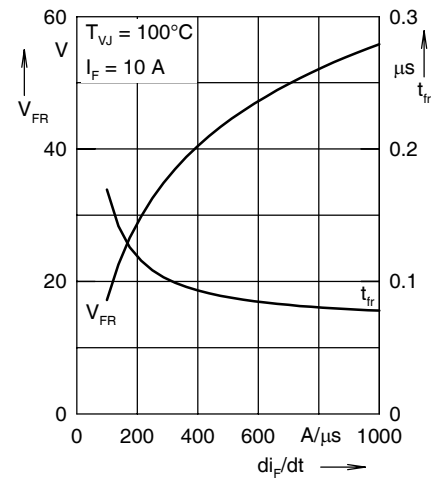


Fig. 23. Peak forward voltage V_{FR} and t_{fr}

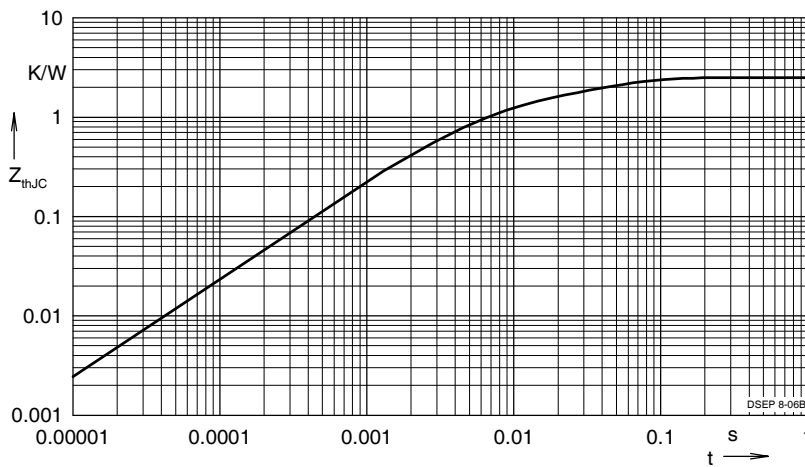


Fig. 24. Transient thermal resistance junction-to-case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	1.449	0.0052
2	0.5578	0.0003

NOTE: Fig. 18 to Fig. 23 shows typical values

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